

EAST Search History (6 pp.) ~~48~~

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	100	esd and (buried adj (layer region)) and bipolar adj transistor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:36
L2	58	esd.ti,ab,clm. and (buried adj (layer region)) and bipolar adj transistor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:36
S1	5	"498677".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/20 08:27
S2	32	(bidirectional bi-directional two-way comprehensive unified) near3 (electrostatic adj discharge esd).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 14:56
S3	30	steinhoff.in. and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:08
S4	2190	(esd electrostatic adj discharge).ti, ab,clm. and transistor and terminal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:09
S5	166	(esd electrostatic adj discharge).ti, ab,clm. and transistor and terminal and (bidirectional bi-directional "two way"\$1 comprehensive unified)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:10
S6	53	(esd electrostatic adj discharge).ti, ab,clm. and transistor and terminal and (bidirectional bi-directional "two way"\$1 comprehensive unified) and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:22
S7	218	common near4 "source/drain" and gate near4 connect\$3 near4 source and gate near4 connect\$3 near4 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:25

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S8	126	common near4 "source/drain" and gate near4 connect\$3 near4 source and gate near4 connect\$3 near4 drain and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:25
S9	2408	257/355	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S10	1058	257/356	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S11	1139364	"57"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S12	7749759	"8"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S13	1179	257/360	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S14	3567	((257/173) or (257/355) or (257/356) or (257/357) or (257/358) or (257/359) or (257/360)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:27
S15	16	S14 and protection adj circuit near10 ((cmos cmosfet) near4 (inverter invertor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:28
S16	17	S14 and protection adj circuit near10 ((cmos cmosfet) near4 (inverter invertor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:58
S17	1822	(257/355).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:58

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S18	207	S17 and inverter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 16:00
S19	103	S17 and inverter and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 16:13
S20	365	esd adj protection adj circuit and integrated adj circuit and (CMOS CMOSFET invert?r) and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 16:14
S21	454	esd adj protection adj circuit and integrated adj circuit and (BiCMOS CMOS CMOSFET invert?r) and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:08
S22	2	("6784496").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:13
S23	4	"407037".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:14
S24	2	("6919603").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:16
S25	2	("6919603").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:16
S26	2	("6577481").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:17
S27	0	("690006.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:18

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S28	0	("690011.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:18
S29	0	("6692606.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:19
S30	2	("6949800").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:19
S31	2	("6933741").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:20
S32	2	("7060538").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:21
S33	16	S22 S23 S24 S25 S26 S27 S28 S29 S30 S31 S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:23
S34	6	(US-7060538-\$ or US-6949800-\$ or US-6919603-\$ or US-6784496-\$ or US-6577481-\$).did. or (US-6784496-\$).did.	USPAT; DERWENT	OR	OFF	2006/09/19 17:25
S35	13	(bidirectional bi-directional) and ESD and biCMOS and SCR	USPAT; DERWENT	OR	ON	2006/09/19 17:53
S36	16	(bidirectional bi-directional) and ESD and biCMOS and SCR	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:56
S37	326	(257/358).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 18:23

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S38	1	"6369427".pn. and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 18:29
S39	190	esd adj protection and cmos adj inverter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 18:29
S40	198	esd adj protection and cmos adj inverter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:29
S41	123	esd adj protection and cmos adj inverter and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:30
S42	2	"6369427".pn. and (ground terminal reference)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/20 08:57
S43	1	"6369427".pn. and (substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/20 09:04
S44	1	esd and inverter and (duf buried) and (semiconductor silicon) adj substrate and sinker	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 09:17
S45	0	esd and inverter and (duf) and (semiconductor silicon) adj substrate and sinker	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 09:17
S46	0	esd and (duf) and (semiconductor silicon) adj substrate and sinker	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 09:17
S47	0	esd and (duf) and (semiconductor silicon) adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 09:17

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S48	236	esd and (buried adj (layer region)) and (semiconductor silicon) adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:35
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